PNP/NPN Epitaxial Planar Silicon Transistors



2SB1136/2SD1669

50V/12A Switching Applications

Applications

· Relay drivers, high-speed inverters, converters, and other genral high-current switching applications.

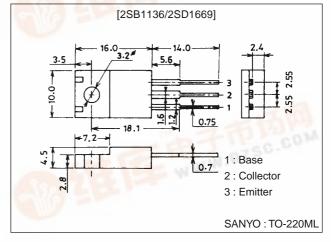
Features

- · Low-saturation collector-to-emitter voltage : $V_{CE(sat)}$ =-0.5V (PNP), 0.4V (NPN) max.
- · Wide ASO leading to high resistance to breakdown.
- · Micaless package facilitating mounting.

Package Dimensions

unit:mm

2041A



(): 2SB1136

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	l _C		(-)12	Α
Collector Current (Pulse)	I _{CP}	1 A.D. (185)	(–)15	Α
Collector Dissipation	PC	AND A PER VEN	2	W
		Tc=25°C	30	W
Junction Temperature	Tj	FR0 8	150	°C
Storage Temperature	Tstg	DEA	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)40V, I _E =0			(-)0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)0.1	mA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)1A	70*	-11	280*	.014
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)5A	30	- o7	50.	
Gain-Bandwidth Product	f _T	V _{CE} =(-)5V, I _C =(-)1A	W Los	10		MHz
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)6A, I _B =(-)0.6A			(-)0.4	V

*: The 2SB1136/2SD1669 are classified by 1A hFE as follows:

70 Q 140 100 R 200 140 S 280

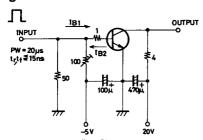
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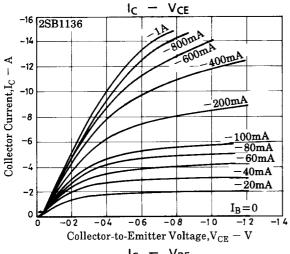
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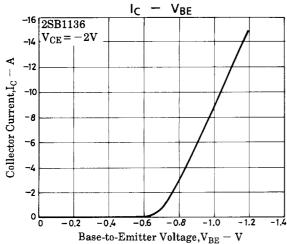
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)1mA, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(-)1mA, R _{BE} =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)1mA, I _C =0	(–)6			V
Rise Time	ton	See specified Test Circuti.		(0.2)		μs
				0.1		μs
Storage Time	t _{stg}	See specified Test Circuit.		(0.4)		μs
				1.2		μs
Fall Time	t _f	See specified Test Circuit.		(0.1)		μs
				0.05		μs

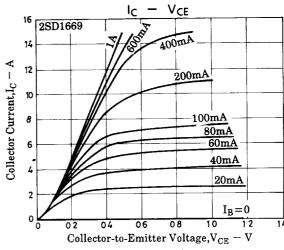
Switching Time Test Circuit

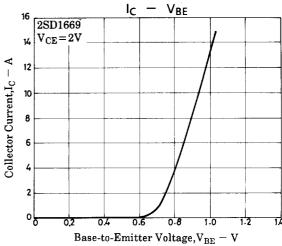


 $10I_{B1} = -10I_{B2} = I_C = 2A$ (For PNP, the polarity is reversed.) Unit (resistance : Ω , capacitance : F)

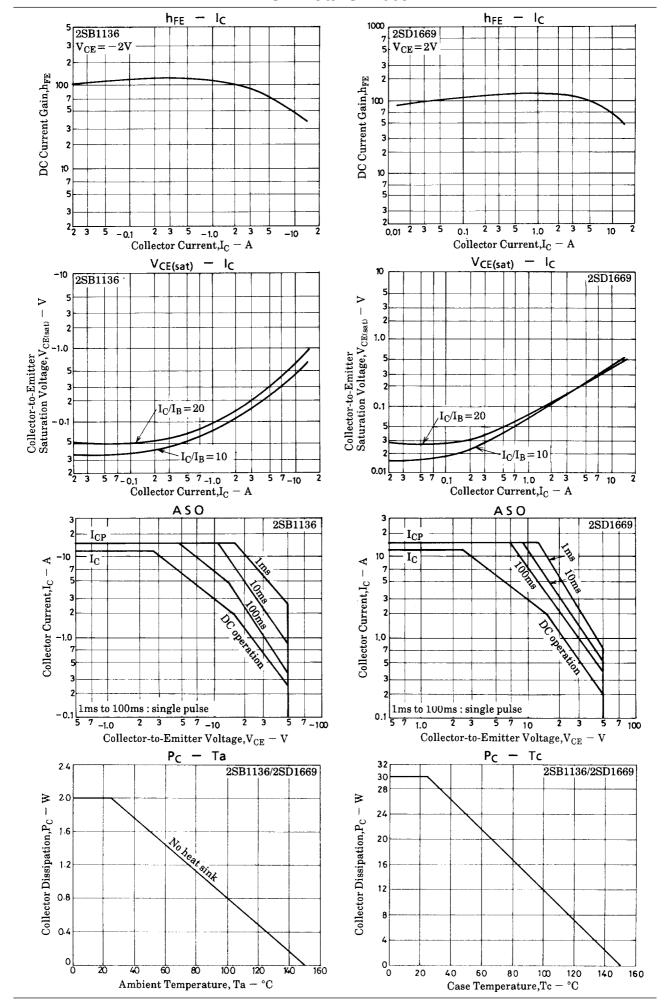








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